



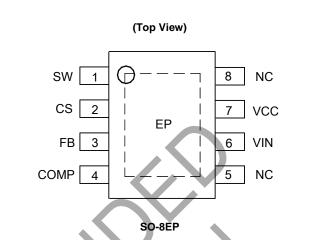
### Description

The DIODES<sup>™</sup> AL8821 is a boost converter that delivers an accurate constant current for MR16 and similar LED lamps. With proprietary control scheme, the LED driver is compatible with many commonly used electronic transformers and provides designs with High Power Factor (PF) and low Total Harmonic Distortion (THD) for these applications. The operation frequency is up to 1MHz that allows the use of small size inductor. With the package of SO-8EP, the AL8821 has small thermal resistance and can be used for wide range of output power. The driver can be used for dimmable MR16 application and can be compatible with leading-edge dimmer and trailing-edge dimmer.

### Features

- Wide Input Voltage Range: 5V to 36V
- Internal 50V NDMOS Switches
- Continuous Conduction Mode (CCM) Operation
- Up to 1MHz Switching Frequency
- High PF > 0.9 and Low THD < 30% and Low Ripple < 20%
- Compatible with Leading-Edge Dimmer and Trailing-Edge
  Dimmer
- Internal Protections
  - Under Voltage Lock Out (UVLO)
  - Output Open
  - Over Temperature Protection (OTP)
- Pb-free SO-8EP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/guality/product-definitions/</u>

## Pin Assignments



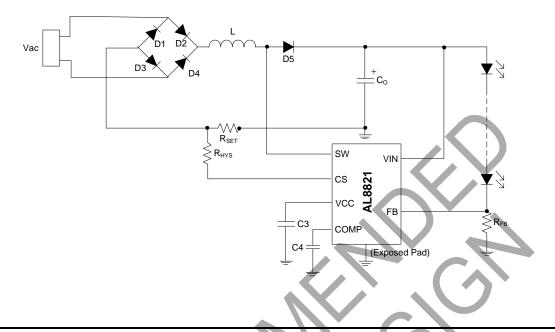
### Applications

- Non-dimmable MR16 lamps
- Dimmable MR16 lamps
- General illumination lamps

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



# **Typical Applications Circuit**



# **Pin Descriptions**

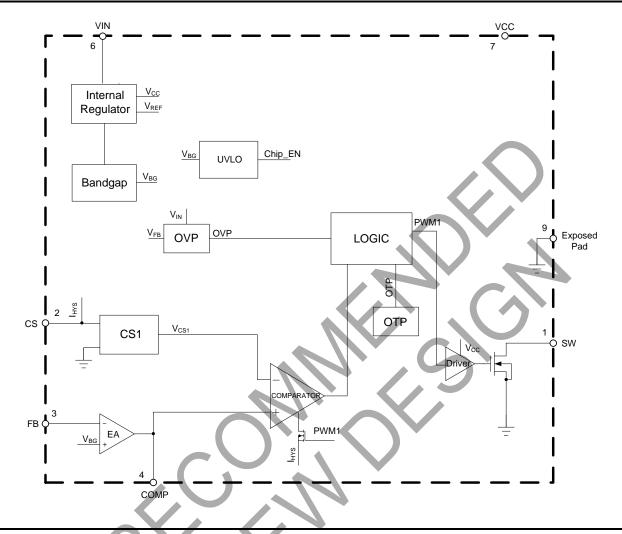
Pin Number	Pin Name	Function
1	SW	Integrated MOS Drain
2	CS	Input Current Sense Pin
3	FB	LED Output Current Feedback Pin
4	COMP	Control Loop Compensation Pin
5	NC	Not Connected
6	VIN	IC Input Voltage, Adding from Boost Output Voltage
7	VCC	Supply Voltage for Internal Circuit
8	NC	Not Connected
EP	Exposed Pad	Connected to Ground

4





## **Functional Block Diagram**



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 4)

Symbol	Parameter	Rating	Unit		
Vin	VIN Pin Voltage	-0.3 to 40	V		
Vsw	SW Pin Voltage	-0.3 to 50	V		
VCOMP	COMP Pin Voltage	in Voltage-0.3 to 40in Voltage-0.3 to 50P in Voltage-0.3 to 6n Voltage-0.3 to 6n Voltage-0.3 to 6n Voltage-0.3 to 6Pin Voltage-0.5 to +150pe Temperature-65 to +150nal Resistance (Junction to Ambient) (Note 5)66Temperature (Soldering, 10sec)+300			
Vcs	CS Pin Voltage	-0.3 to 6	V		
VFB	FB Pin Voltage	-0.3 to 6	V		
Vcc	VCC Pin Voltage	-0.3 to 6	V		
TJ	Operating Junction Temperature	IP Pin Voltage-0.3 to 6Pin Voltage-0.3 to 6Pin Voltage-0.3 to 6Pin Voltage-0.3 to 6rating Junction Temperature+150age Temperature-65 to +150mal Resistance (Junction to Ambient) (Note 5)66Temperature (Soldering, 10sec)+300			
Тѕтс	Storage Temperature	in Voltage-0.3 to 50P Pin Voltage-0.3 to 6n Voltage-0.3 to 6n Voltage-0.3 to 6Pin Voltage			
θ <sub>JA</sub>	Thermal Resistance (Junction to Ambient) (Note 5)	66	°C/W		
TLEAD	Lead Temperature (Soldering, 10sec)	+300	°C		
_	ESD (Machine Model)	200	V		
	ESD (Human Body Model)	2000	V		

Notes: 4. Stresses greater than those listed under Absolute Maximum Ratings can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to Absolute Maximum Ratings for extended periods can affect device reliability.

 Device mounted on FR-4 PCB (51mm x 51mm) 2oz copper, minimum recommended pad layout on top layer and thermal vias to bottom layer ground plane. For better thermal performance, larger copper pad for heat-sink is needed.



# **Recommended Operating Conditions**

Symbol	Parameter	Min	Мах	Unit
V <sub>IN</sub>	VIN Pin Voltage	5	36	V
TA	Ambient Temperature	-40	+105	°C

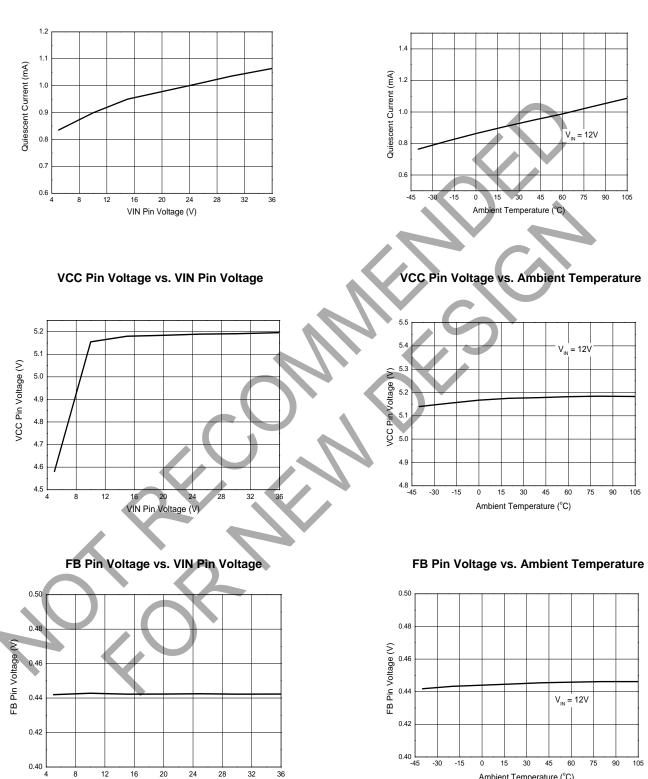
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameters	Conditions	Min	Тур	Max	Unit
Input Supply			•			
Vin	VIN Pin Voltage	—	5		36	V
la	Quiescent Current	No Switching		1	_	mA
Vuvlo	Under-Voltage Lockout Voltage	VIN Rising	—	4.2	-	V
VHYS	UVLO Hysteresis	-		500	—	mV
VCC Regulator						
Vcc	VCC Pin Voltage	-	4.5	5	5.5	V
_	Source Current Capability	$V_{CC} = 5V$	10		—	mA
_	Load Regulation	-		4	_	%
Integrated NMOS_BOOST						
V <sub>DS</sub>	MOS Voltage Stress (Note 6)	+		50	_	V
I <sub>DS</sub>	MOS Current Stress (Note 6)	_		2	_	А
Rdson	MOS RDSON			250	—	mΩ
Compensation and Soft Star	rt (COMP Pin)					
GEA	Error Amplifier Trans- Conductance		_	1000	_	μA/V
Іо-н	Sourcing Current	VCOMP = 0.5V	—	68	—	μA
I <sub>O-L</sub>	Sinking Current	$V_{COMP} = 4.5V$	—	68	—	μA
Vfb	FB Pin Voltage	<u>~</u>	—	444	—	mV
Hysteresis Competitor						
Vcs_min	Boost Sense Voltage Low Level	V <sub>COMP</sub> = 0V	_	-90	_	mV
Інуз	Hysteresis Current	—	85	100	115	μA
<b>Over-Temperature Protectio</b>	n					
Тотяр	Thermal Shutdown (Note 6)	_		+160		°C
Тнуз	Thermal Shutdown Hysteresis (Note 6)	—	_	+40	_	°C

Note: 6. These parameters, although guaranteed by design, are not 100% tested in production.



### **Performance Characteristics**



**Quiescent Current vs. Ambient Temperature** 

8

12

16

20

VIN Pin Voltage (V)

24

28

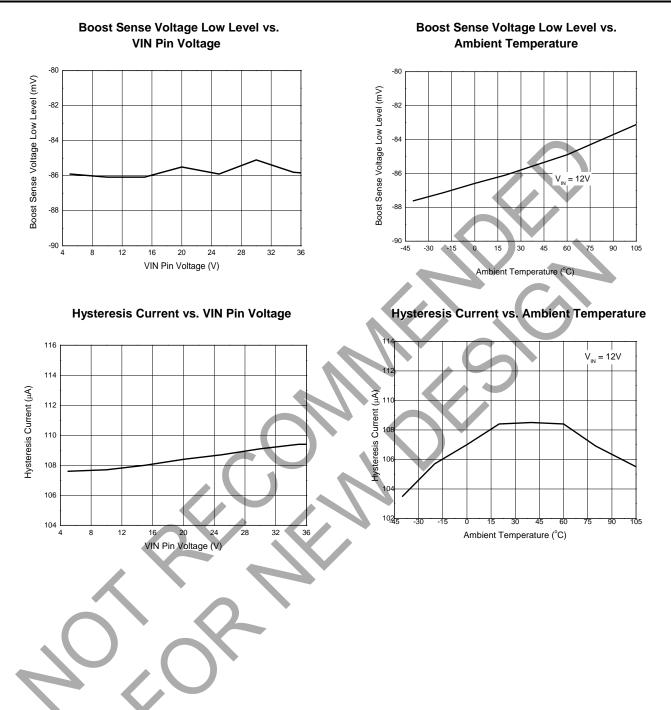
32

36

Ambient Temperature (°C)



# Performance Characteristics (continued)

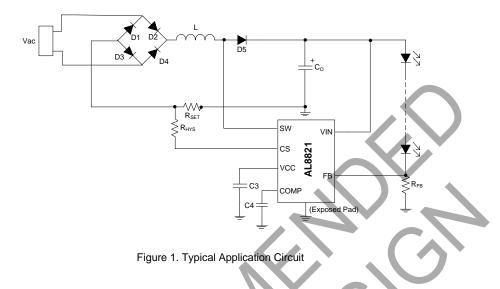




### **Application Information**

### AL8821 Operation

The AL8821 is a boost converter that delivers an accurate constant current for driving LEDs. With hysteretic control scheme, the LED driver is compatible with most of commonly used electronic transformers. The driver can be compatible with leading-edge dimmer and trailing-edge dimmer.



#### **LED Current Control**

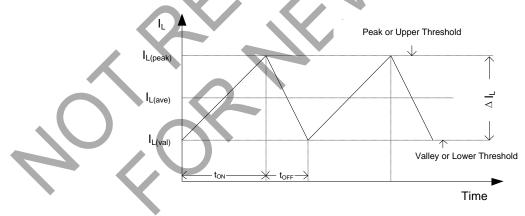
The LED current is controlled by the resistor RFB in Figure 1.

Connected between FB pin and Ground, the nominal average output current in the LED(s) is defined as:

$$I_{LED} = \frac{0.444V}{R_{FB}}$$

#### **RSET and RHYS Setting**

The Boost converter of the AL8821 operates at continuous conduction mode and is based on hysteresis schematic which has lower threshold and upper threshold. Refer to Figure 2 depicting the inductor current waveform.



### Figure 2. Inductor Current

When switch SW is turned on, the inductor current flows through  $R_{SET}$  and ramps up linearly. The rising current produces a voltage ramp across  $R_{SET}$ . When the voltage across  $R_{SET}$  reaches the upper threshold, switch SW is turned off. The inductor current continues to flow through  $R_{SET}$  but decays. The decaying current produces a falling voltage at  $R_{SET}$ . When the voltage across  $R_{SET}$  falls to the lower threshold, switch SW is turned on again.

The lower threshold voltage V<sub>LT</sub> depends on the voltage V<sub>COMP</sub> at COMP pin that varies with the input voltage and output load. The equation is shown as below.



### Application Information (continued)

$$V_{LT} = \begin{cases} \frac{(V_{COMP} - 1.5) \times 0.6 + 1.4}{16} V, 1.5V \le V_{COMP} \le 5V \\ 0.088V, 0V \le V_{COMP} \le 1.5V \end{cases}$$

The range of  $V_{COMP}$  is from 0V to 5V.

The upper threshold depends on the lower threshold and the hysteresis value. The hysteresis value is set by external resister R<sub>HYS</sub>. It is defined as below.

$$V_{HYS} = R_{HYS} \times 100 \mu A$$

According to the operation principle, the peak to peak current  $\Delta I_L$  and the valley current  $I_{L(val)}$  can be obtained by the below equations.

$$I_{L(val)} = \frac{V_{LT}}{R_{SET}}$$

$$\Delta I_L = \frac{V_{HYS}}{R_{SET}}$$

Where:  $\Delta I_L$  is the peak to peak current of inductor.

 $I_{L\left( \text{val}\right) }$  is the valley current of inductor.

From the Figure 2, the relationship between  $I_{L(peak)}$ ,  $I_{L(val)}$ ,  $I_{L(ave)}$  and  $\Delta I_{L}$  can be obtained as below.

$$I_{L(peak)} = I_{L(val)} + \Delta I_{L}$$

$$I_{L(ave)} = I_{L(val)} + \frac{1}{2} \times \Delta I_{L}$$

Where:

 $I_{L(peak)}$  is the peak current of inductor.

 $I_{L(ave)}$  is the average current of inductor.

As we know the average current  $I_{L(ave)}$  depends on the output power, rated input voltage  $V_{IN1}$  of step-up converter and total efficiency  $\eta$ . So the average current  $I_{L(ave)}$  can be obtained by the following equation.

$$I_{L(ave)} = \frac{(V_{LED} + 0.444) \times I_{LED}}{\eta \times V_{IN1}}$$

Where:  $\ensuremath{\mathsf{V}_{\mathsf{LED}}}$  is the voltage in LEDs.

Set ratio of  $\Delta I_L$  to  $I_{L(peak)}$  as K.

AL8821 Document number: DS37671 Rev. 3 - 3



## Application Information (continued)

$$K = \frac{\Delta I_L}{I_{L(peak)}}$$

RSET and RHYS can be obtained from above equations:

$$R_{SET} = \begin{cases} \frac{((V_{COMP} - 1.5) \times 0.6 + 1.4) \times (2 - K) \times \eta \times V_{IN1}}{32 \times (V_{LED} + 0.444) \times I_{LED} \times (1 - K)}, 1.5V \le V_{COMP} \le 5V \\ \frac{0.044 \times (2 - K) \times \eta \times V_{IN1}}{(V_{LED} + 0.444) \times I_{LED} \times (1 - K)}, 0V \le V_{COMP} \le 1.5V \end{cases}$$

$$R_{HYS} = \frac{2 \times (V_{LED} + 0.444) \times I_{LED} \times K \times R_{SET} \times 10^4}{\eta \times V_{IN1} \times (2 - K)}$$

When the value of K,  $\eta$  and V<sub>COMP</sub> are provided, the value of resister R<sub>SET</sub> and R<sub>HYS</sub> can be calculated according to these above equations. In order to get appropriate efficiency and Electronic Transformer (ET) compatibility, generally K is set between 0.4 and 0.8. Due to the range of V<sub>COMP</sub> is from 0V to 5V, in order to get output voltage regulation, generally V<sub>COMP</sub> is set as 3V at rated input voltage.

### Inductor Selection

Because of the using of the hysteretic control scheme, the switching frequency in a boost configuration can be adjusted in accordance to the value of the inductor being used. The value of the inductor can be determined on the desired switching frequency by using the following equation:

$$L = \frac{[V_{IN1} - (R_{SET} + R_L + R_{DSON}) \times I_{L(ave)}] \times [V_{LED} + 0.444 + V_F + (R_L + R_{SET}) \times I_{L(ave)} - V_{IN1}]}{\Delta I_L (V_{LED} + 0.444 + V_F - R_{DSON} \times I_{L(ave)}) \times f_{SW}}$$

Where:

L is the coil inductance.

 $R_L$  is the coil resistance.

RDSON is the switch SW resistance.

VIN1 is the rated input voltage.

VF is the diode forward voltage.

fsw is the desired switching frequency. Generally 500kHz to 800kHz switching frequency is suggested. Low switching frequency can decrease the switching loss but need to choose higher inductor values that will result in larger size in order to meet the saturation current. For example the relationship between switching frequency and inductor value is shown as below Table 1 in the same application system. Considering these factors, 500kHz switching frequency is recommended in typical application.

Inductance Value of L @ Vac = 12Vac, V <sub>IN</sub> = 22V $V_{LED} = 28V$ , I <sub>LED</sub> = 180mA	Operation Frequency of SW at Peak Voltage Of Vac		
10µH	840kHz		
15µH	800kHz		
22µH	680kHz		
33µН	465kHZ		

Table 1



### Application Information (continued)

#### VIN OVP Protection

AL8821 has an internal over voltage protection to protect IC from excessive input voltage. When the voltage applied at VIN pin exceeds 39V, it will turn off the power switch SW. The power switch SW will be turned on again once the voltage at VIN drops below 34V.

#### VCC Regulator

The VCC pin requires a capacitor C3 for stable operation and to store the charge for the large GATE switching currents. Choose a 10V rated low ESR, X7R or X5R, ceramic capacitor for best performance. A 4.7µF capacitor will be adequate for many applications. Place the capacitor close to the IC to minimize the trace length to the VCC pin and to the IC ground.

An internal current limit on the VCC output protects the excessive on-chip power dissipation. The VCC pin has set the output to 5V (typ.) to protect the internal FETs from excessive power dissipation caused by not being fully enhanced. If the VCC pin is used to drive extra circuits beside the AL8821, the extra loads should be limited to less than 8mA.

#### Output Capacitor Co

The capacitor Co is used to hold the bus voltage and reduce the ripple of LED current when the electronic transformer has no output. For most applications, it is recommended to use an aluminum electrolytic capacitor with greater than 220µF capacitance.

### **Compensation Capacitor C4**

In applications powered by electronic transformer, the input voltage can change roughly in one cycle of AC power frequency. A 1µF ceramic capacitor C4 connected from COMP pin to ground helps to stabilize the control loop of the regulator.

#### **Diode Selection**

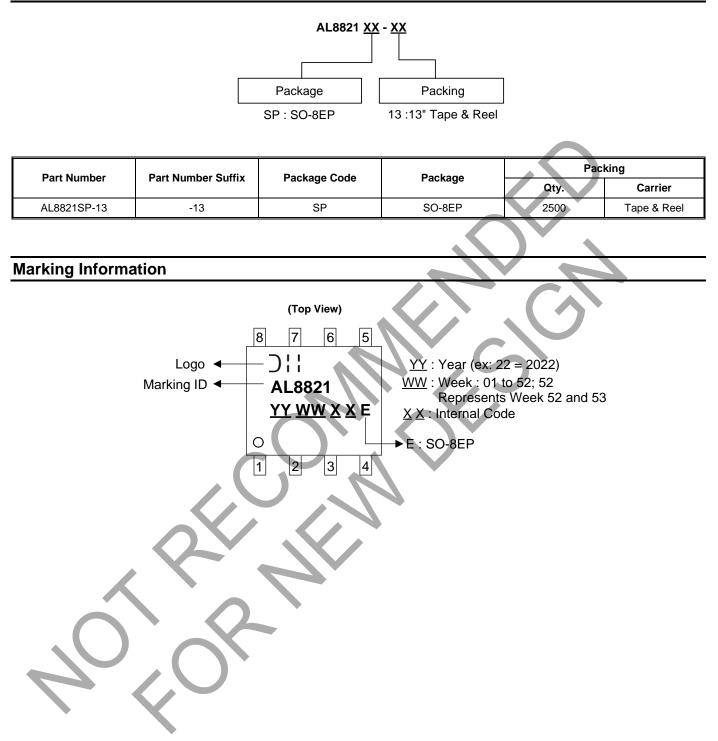
For maximum efficiency and performance, the rectifiers (D5) should be fast low capacitance Schottky diodes with low reverse leakage at maximum operating voltage and temperature. With its low power dissipation, the Schottky diode outperforms other silicon diodes and increases overall efficiency.

#### **Over Temperature Protection**

An over temperature protection feature is to protect the AL8821 from excessive heat damage. When the junction temperature exceeds +160°C, the internal FET will be turned off. When junction temperature drops below +120°C, IC will turn on both FETs and return to normal operation.



## **Ordering Information**

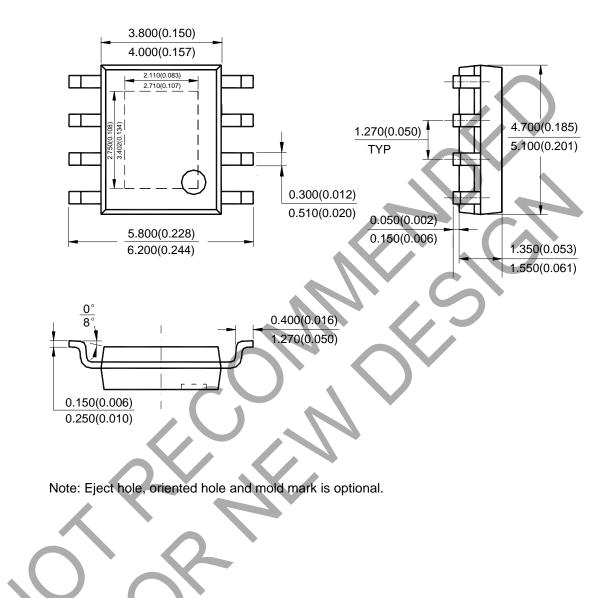




# Package Outline Dimensions (All dimensions in mm(inch).)

Please see http://www.diodes.com/package-outlines.html for the latest version.

### Package Type: SO-8EP

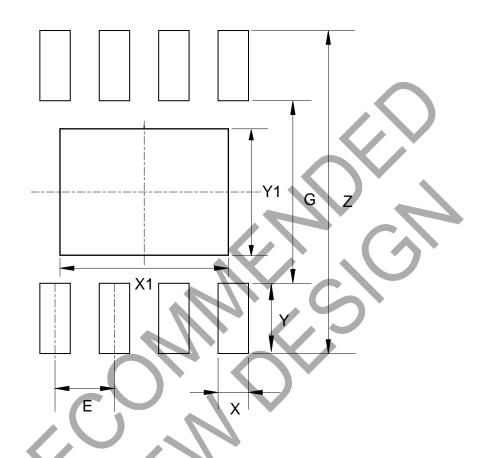




# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### Package Type: SO-8EP



Dimensions	Z	G	X	Y	X1	Y1	E
	(mm)/(inch)						
Value	6.900/0.272	3.900/0.154	0.650/0.026	1.500/0.059	3.600/0.142	2.700/0.106	1.270/0.050





#### IMPORTANT NOTICE

1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (<u>https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/</u>) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

9. This Notice may be periodically updated with the most recent version available at <a href="https://www.diodes.com/about/company/terms-and-conditions/important-notice">https://www.diodes.com/about/company/terms-and-conditions/important-notice</a>

DIODES is a trademark of Diodes Incorporated in the United States and other countries. The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. © 2022 Diodes Incorporated. All Rights Reserved.

www.diodes.com